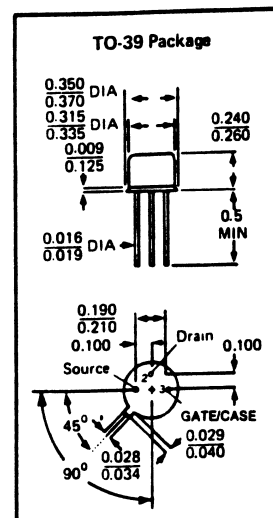


- HIGH $V_{GSS} \dots 300V$ MIN (2N6449)
- HIGH POWER RATING $\dots 5W$

ELECTRICAL DATA ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	2N6449	2N6450	UNITS
Drain to Gate Voltage	BV_{DGO}	300	200	Volts
Gate to Source Voltage	BV_{GSO}	-300	-200	Volts
Power Dissipation (25°C case)	P_{DC}	5		W
Derating Factor (Junction to Case)	DFC	3.33		mW/°C
Power Dissipation (free air)	P_{DA}	800		mW
Derating Factor (free air)	DFA	5.33		mW/°C
Junction Temp. (Oper. & Store)	T_J	-65 to 200		°C
Lead Temp. (1/16" From Case 10 sec)	T_L	300		°C
Continuous Forward Gate Current	I_{GF}	10		mA



ELECTRICAL CHARACTERISTICS: $T_A = 25^\circ C$ (UNLESS OTHERWISE STATED)

PARAMETERS AND CONDITIONS	SYMBOL	2N6449			2N6450			UNITS
		Min.	Typ.	Max.	Min.	Typ.	Max.	
Gate Leakage Current $V_{GS} = -150V, V_{DS} = 0$	I_{GSS}		-1	-10				nA
Gate Leakage Current $V_{GS} = -150V, V_{DS} = 0, T_A = 150^\circ C$	I_{GSS}		-1	-10				μA
Gate Leakage Current $V_{GS} = -100V, V_{DS} = 0$	I_{GSS}		-1			-1	-10	nA
Gate Leakage Current $V_{GS} = -100V, V_{DS} = 0, T_A = 150^\circ C$	I_{GSS}		-1			-1	-10	μA
Gate Breakdown Voltage $I_G = -10\mu A, V_{DS} = 0$	BV_{GSS}	-300			-200			V
Pinch-Off Voltage $V_{DS} = 30V, I_D = 4nA$	V_{PO}	-2		-15			-15	V
Zero Bias Drain Current $V_{DS} = 30V, V_{GS} = 0$	I_{DSS}^1	2		10	2		10	mA
Forward Transfer Admittance $V_{DS} = 30V, V_{GS} = 0, f = 1 kHz$	Y_{fs}^2	500		3000	500		3000	μmho
Output Admittance $V_{DS} = 30V, V_{GS} = 0, f = 1 kHz$	Y_{os}^2			100			100	μmho
Input Capacitance $V_{DS} = 30V, V_{GS} = 0, f = 1 kHz$	C_{iss}^2			10			10	pf
Reverse Xfer Cap. $V_{DS} = 30V, V_{GS} = 0, f = 1 kHz$	C_{rss}^2			5			5	pf

- NOTES: 1. Measured using pulse techniques, $t_w = 300\mu s$, duty cycle $< 2\%$.
2. Measured with bias conditions applied for less than 5 seconds.

